

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Max R _{DS(ON)}	I _D Max T _A = +25°C
201/	460mΩ @ V _{GS} = 4.5V	0.9A
30V	560mΩ @ V _{GS} = 2.5V	0.83A

Features and Benefits

- Low V_{GS(TH)}, can be Driven Directly from a Battery
- Low R_{DS(ON)}
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Load Switch
- Portable Applications
- Power Management Functions

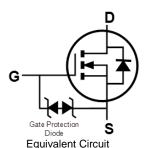
Mechanical Data

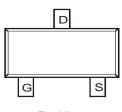
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ©3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)





Top View





Top View Pin-Out

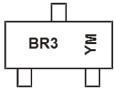
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per Reel
DMN3731U-7	BR3	7	3,000
DMN3731U-13	BR3	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BR3 = Product Type Marking Code YM or YM = Date Code Marking Y or Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	201	8	2019		2020	20	21	2022		2023	2	2024
Code	F		G		Н			J		K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±8	V
I Continuous Drain Current (Note 6) Voc - 4 5V		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ΙD	0.9 0.7	А
Maximum Continuous Body Diode Forward Curre	Is	0.55	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle =	I _{DM}	3	A		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	303	°C/W
Total Power Dissipation (Note 6)		P_D	0.58	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	215	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = 25°C unless otherwise specified)

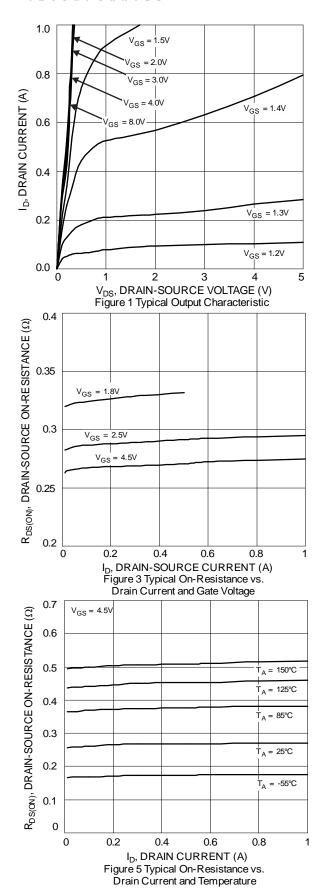
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	- Cymber		. , , ,	max	<u> </u>	root containen
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		_	3	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						•
Gate Threshold Voltage	V _{GS(TH)}	0.45	_	0.95	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			271	460		$V_{GS} = 4.5V, I_D = 200mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	288	560	mΩ	$V_{GS} = 2.5V, I_D = 100mA$
	, ,		324	730		$V_{GS} = 1.8V, I_D = 75mA$
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						•
Input Capacitance	C _{iss}		73	_	pF	N 051/ N 01/
Output Capacitance	Coss	_	7.2	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		5	_	pF	1 = 1.01/11 12
Gate Resistance	Rg	_	902	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg	_	5.5	_	nC	4514.14
Gate-Source Charge	Q _{qs}		0.8	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$
Gate-Drain Charge	Q _{qd}		1.4	_	nC	$I_D = 1A$
Turn-On Delay Time	t _{D(ON)}		2.5	_	ns	
Turn-On Rise Time	t _R	_	3.1	_	ns	$V_{DS} = 10V, I_{D} = 1A$
Turn-Off Delay Time	t _{D(OFF)}		477	_	ns	$V_{GS} = 10V, R_q = 6\Omega$
Turn-Off Fall Time	t _F		123	_	ns]
Reverse Recovery Time	t _{RR}		59	_	ns	1. 10. 17/1/2 1000/
Reverse Recovery Charge	Q _{RR}		25	_	nC	I _F = 1A, di/dt = 100A/μs

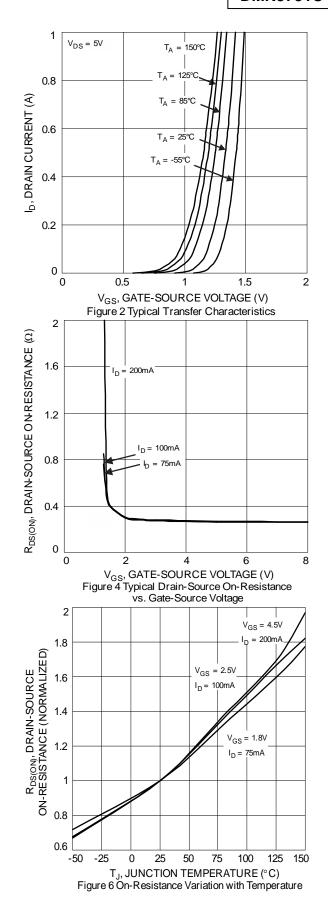
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.

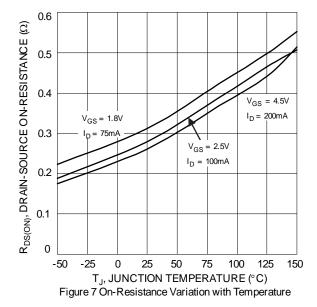
- 8. Guaranteed by design. Not subject to production testing.

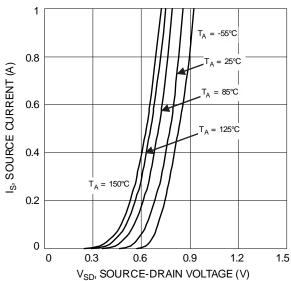


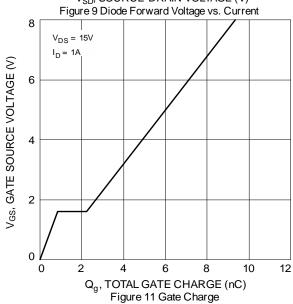


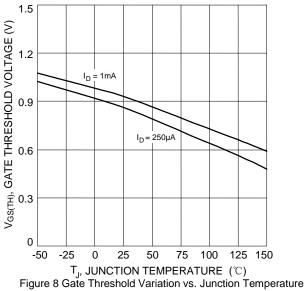


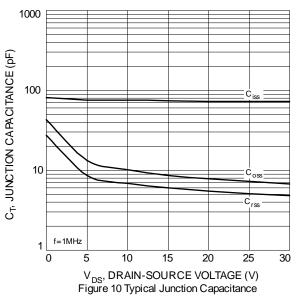












10 R_{DS(on)} Limited I_D, DRAIN CURRENT (A) 0.1 0.01 T_{J(max)} = 150°C

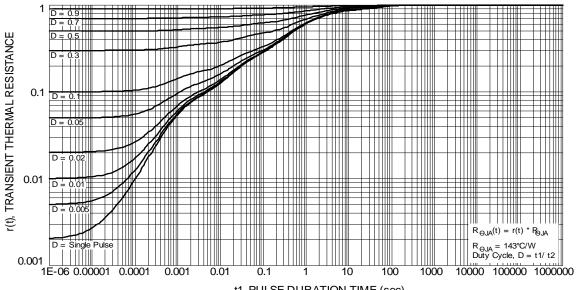
T_C = 25°C

V_{GS} = 4.5V

Single Pulse
DUT on 1*MRP Board 0.001 10 100 0.1

·V_{DS} DRAIN-SOURCE VOLTAGE (V) Figure # SOA, Safe Operation Area



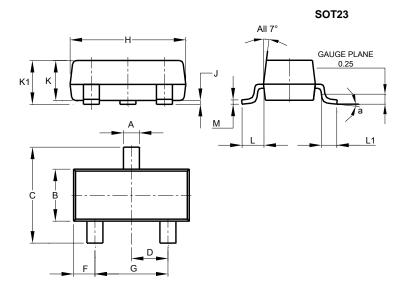


t1, PULSE DURATION TIME (sec) Figure 13 Transient Thermal Resistance



Package Outline Dimensions

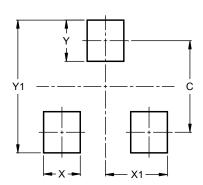
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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